

In the claims:

Rewrite claim 20 in independent form as follows:

20. (Amended) An integrated circuit, comprising:

a first dielectric layer disposed outwardly from a substrate;

a plurality of gate stacks, each gate stack comprising:

a floating gate body disposed outwardly from the first dielectric layer;

a second dielectric region disposed outwardly from the floating gate body; and

a first polysilicon layer disposed outwardly from the second dielectric region;

a plurality of dielectric isolation regions disposed between the gate stacks, the dielectric isolation regions formed after the formation of the gate stacks;

[The integrated circuit of Claim 12, further comprising:] a second polysilicon layer disposed outwardly from the first polysilicon layer and the dielectric isolation regions;

a peripheral dielectric layer disposed outwardly from the second polysilicon layer and a peripheral region of the substrate, the peripheral region of the substrate disposed adjacent to a region of the substrate supporting the gate stacks;

at least one peripheral gate body disposed outwardly from the peripheral region of the substrate.

REMARKS

It is initially noted that claims 1 to 11 were cancelled in the Preliminary Amendment filed with this application. Accordingly, these claims are not and never were effectively present in this application. However, the affirmation of election of claims 12 to 20 is nevertheless provided herewith to avoid any issue in this regard.